

TO-126C Plastic-Encapsulate Transistors

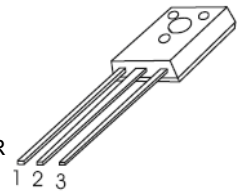
2SB776 TRANSISTOR (PNP)

FEATURES

- High Current Output up to 3A
- Low Collector-Emitter Saturation Voltage
- Complement to 2SD886

TO – 126C

1. EMITTER
2. COLLECTOR
3. BASE



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-3	A
P_C	Collector Power Dissipation	1	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	125	$^\circ\text{C/W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-5\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50\text{V}, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-3\text{V}, I_C=0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2\text{V}, I_C=-20\text{mA}$	100			
	$h_{FE(2)}$	$V_{CE}=-2\text{V}, I_C=-1\text{A}$	100		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2\text{A}, I_B=-200\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2\text{A}, I_B=-200\text{mA}$			-2	V
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		45		pF
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-100\text{mA}$		80		MHz

*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycles $\leq 2.0\%$.